

4-bit Single Chip Microcomputer



- 4-bit E0C63000 Core CPU
- A/D Converter
- Built-in LCD Driver
- High Speed Instruction Cycle (2-6CPI)

■ DESCRIPTION

The E0C63256 is a microcomputer composed of a CMOS 4-bit core CPU (E0C63000), ROM, RAM, LCD driver and timers. Since the E0C63000 core CPU executes the principle instructions in 1 or 2 cycles, it is suitable for various high-speed controller. Furthermore, the E0C63256 has built-in four-channel 8-bit A/D converter and is most suitable for applications such as control units for household electric appliances which need A/D conversion and liquid crystal display.

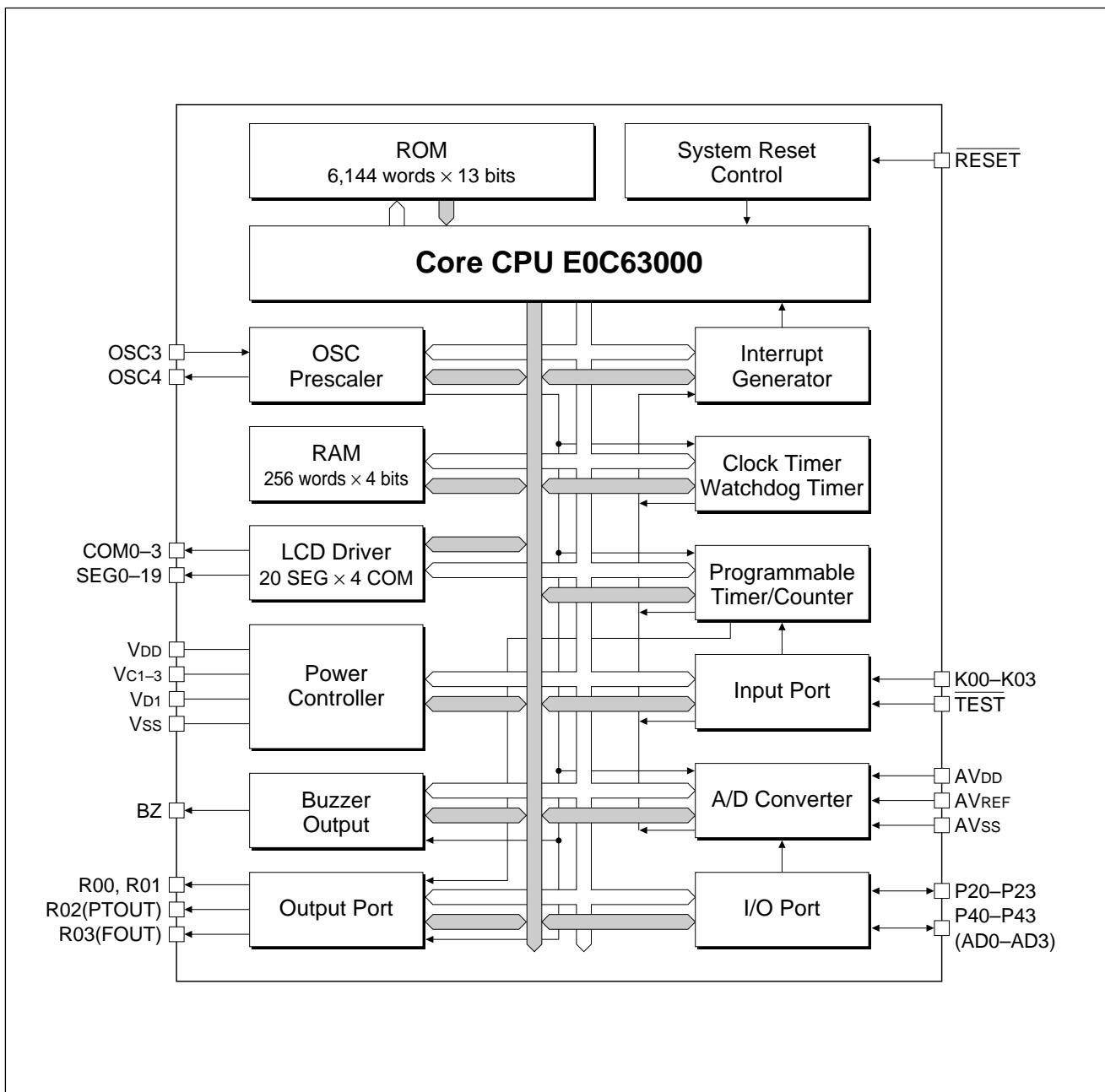
■ FEATURES

- CMOS LSI 4-bit parallel processing
- Clock 0.5MHz to 4.5MHz (Ceramic, X'tal or CR oscillation)
- Instruction set Basic instruction : 46 types (411 instructions with all)
Addressing mode : 8 types
- ROM capacity 6,144 words × 13 bits
- RAM capacity 256 words × 4 bits
- Input port 4 bits
- Output port 4 bits
- I/O port 8 bits
- LCD driver 20 segments × 4/3/2 commons
- Clock timer 1 ch.
- Programmable timer 8 bits × 4 ch., 8 bits × 2 ch. and 16 bits × 1 ch. (Selective)
- Watchdog timer Built-in
- A/D converter 8 bits × 4 ch.
- Supply voltage detection (SVD) circuit From 1.05 to 2.60V
- Operation voltage 2.7 to 5.5V
- Current consumption 620µA (4.193MHz, X'tal, HALT)
1.5mA (4.193MHz, X'tal, RUN)
60µA (LCD current, 3.0V) *1
100µA (LCD current, 5.0V) *1
- Package QFP13-64pin, Die form

*1: Add to current consumption

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■ BLOCK DIAGRAM



■ PIN CONFIGURATION

QFP13-64pin		No.	Pin name						
1	SEG13	17	RESET	33	N.C.	49	COM2		
2	SEG14	18	TEST	34	BZ	50	COM3		
3	SEG15	19	Vss	35	R00	51	SEG0		
4	SEG16	20	OSC3	36	R01	52	SEG1		
5	SEG17	21	OSC4	37	R02	53	SEG2		
6	SEG18	22	Vd1	38	R03	54	SEG3		
7	SEG19	23	Vdd	39	P20	55	SEG4		
8	N.C.	24	AVDD	40	P21	56	SEG5		
9	N.C.	25	AVREF	41	P22	57	SEG6		
10	N.C.	26	AVSS	42	P23	58	SEG7		
11	N.C.	27	N.C.	43	K00	59	SEG8		
12	N.C.	28	N.C.	44	K01	60	SEG9		
13	N.C.	29	P40	45	K02	61	SEG10		
14	Vc1	30	P41	46	K03	62	SEG11		
15	Vc2	31	P42	47	COM0	63	SEG12		
16	Vc3	32	P43	48	COM1	64	N.C.		

N.C. : No Connection

■ PIN DESCRIPTION

Pin name	Pin No.	In/Out	Function
VDD	23	-	Power (+) supply pin
Vss	19	-	Power (-) supply pin
AVDD	24	-	Power (+) supply pin for analog circuit system
AVss	26	-	Power (-) supply pin for analog circuit system
AVREF	25	I	Reference voltage input pin for analog circuit system
Vd1	22	-	Oscillation/internal logic system regulated voltage output pin
Vc1, Vc2, Vc3	14, 15, 16	-	LCD system power supply pin 1/3 or 1/2 bias (selected by mask option)
OSC3	20	I	Crystal/ceramic/CR oscillation/external clock input pin (selected by mask option)
OSC4	21	O	Crystal/ceramic/CR oscillation output pin (selected by mask option)
K00-K03	43–46	I	Input port
P20–P23	39–42	I/O	I/O port
P40–P43	29–32	I/O	I/O port (switching to A/D converter input is possible by software)
R00	35	O	Output port
R01	36	O	Output port
R02	37	O	Output port (switching to PTOUT signal output is possible by software)
R03	38	O	Output port (switching to FOUT signal output is possible by software)
COM0–COM3	47–50	O	LCD common output pin (1/4, 1/3, 1/2 duty can be selected by software)
SEG0–SEG19	51–63, 1–7	O	LCD segment output pin
BZ	34	O	Buzzer output pin
RESET	17	I	Initial reset input pin
TEST	18	I	Testing input pin

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■ ELECTRICAL CHARACTERISTICS

● Absolute Maximum Ratings

(Vss=0V)						
Rating	Symbol	Condition	Value	Unit	Note	
Supply voltage	VDD		-0.3 to +7.0	V		
LCD supply voltage	VC		-0.3 to +7.0	V		
Input voltage	VI		-0.3 to VDD+0.3	V		
Output voltage	VO		-0.3 to VDD+0.3	V	1	
High-level output current	IOH	1 terminal	-5	mA		
		Total of all terminals	-20	mA		
Low-level output current	IOL	1 terminal	5	mA		
		Total of all terminals	20	mA		
Operating temperature	Topr		-20 to +85	°C		
Storage temperature	Tstg		-65 to +150	°C		
Soldering temperature / time	Tsol		260°C, 10sec (lead section)	—		
Permissible dissipation	PD		250	mW	2	

Note) 1. It is applied to the output voltage when Nch open drain is selected by mask option.
 2. In case of plastic package.

● Recommended Operating Conditions

(Vss=AVss=0V, Ta=-20 to 85°C)								
Condition	Symbol	Remark	Min.	Typ.	Max.	Unit	Note	
Supply voltage	VDD	VDD	2.7	3.0/5.0	5.5	V		
LCD supply voltage	VC3I	VC3	2.7		5.5	V	1	
	VC3E	VC3	2.7		5.5	V	2	
	VC2E	1/3 bias 1/2 bias	VC2	Typ. - 0.2 Typ. - 0.2	VC3-2/3 VC3-1/2	Typ. + 0.2 Typ. + 0.2	V 2	
	VC1E	1/3 bias 1/2 bias	VC1	Typ. - 0.2 Typ. - 0.2	VC3-1/3 VC3-1/2	Typ. + 0.2 Typ. + 0.2	V 2	
Analog supply voltage	VAVDD	AVDD	2.7		VDD	V		
Analog reference voltage range	VREF	AVREF	2.7		AVDD	V		
Analog input voltage range	VIN	AD0 to AD3 (P40 to P43)	AVss		AVREF	V		
Operating frequency	fosc	VDD=2.7 to 5.5V	Crystal oscillation circuit Ceramic oscillation circuit CR oscillation circuit External clock input	0.5 0.5 0.5 0.5	4.194 4.0 2.0 4.0	4.5 4.5 2.5 4.5	MHz MHz MHz MHz	3,4 3 3 3,5

Note) 1. When "Internal power (external VC3 is used)" is selected by mask option.
 2. When "External power" is selected by mask option.
 3. The CPU uses the clock output from the oscillation circuit as the operating clock.
 4. Crystal oscillator = 4.194304 MHz
 5. When an external clock is input from the OSC3 terminal by setting the mask option, do not connect anything to the OSC4 terminal.

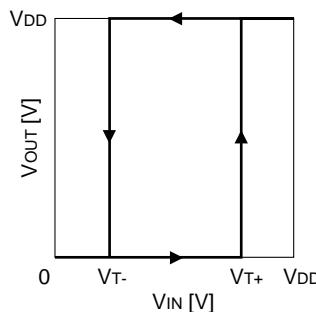
● DC Characteristics

Input Characteristics

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, Ta=-20 to 85°C)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
High-level input voltage	V _{IH1}	K _{xx} , P _{xx}	0.7·V _{DD}		V _{DD}	V	
	V _{IH2}	OSC3	1.7		V _{DD}	V	1
Low-level input voltage	V _{IL1}	K _{xx} , P _{xx}	0		0.3·V _{DD}	V	
	V _{IL2}	OSC3	0		0.7	V	1
High-level schmitt input voltage	V _{T+}	RESET	0.5·V _{DD}		0.9·V _{DD}	V	
Low-level schmitt input voltage	V _{T-}		0.1·V _{DD}		0.5·V _{DD}	V	
Input leak current	I _{LIH}	V _{LIH} =V _{DD}	K _{xx} , P _{xx} , RESET	0		1.0	μA
	I _{LIL}	V _{LIL} =V _{SS}		-1.0		0	μA
Input pull-up resistance	R _{IN}	K _{xx} , P _{xx} RESET	100	250	400	kΩ	2
			250	450	650	kΩ	2
Input terminal capacitance	C _{IN}	V _{IN} =0V, f=1MHz	K _{xx} , P _{xx}		10	15	pF

- Note) 1. When "External clock" is selected by mask option.
 2. When "with pull-up resistor" is selected by mask option.



Output Characteristics

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, V_{C3}=2.7 to 5.5V, V_{C2}/V_{C1} are internal voltage, Ta=-20 to 85°C, C₂=C₃=0.1μF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
High-level output voltage	I _{OH1}	V _{OH1} =0.9·V _{DD} , V _{DD} =5.0V V _{OH1} =0.9·V _{DD} , V _{DD} =3.0V	P _{xx} , R _{xx}	5.3		mA	3
	I _{OH2}			2.5		mA	3
	I _{OH2}	V _{OH2} =0.9·V _{DD} , V _{DD} =5.0V V _{OH2} =0.9·V _{DD} , V _{DD} =3.0V	BZ	5.3		mA	3
	I _{OH3}			2.5		mA	3
	I _{OH3}	V _{OH3} =0.9·V _{DD} , V _{DD} =5.0V V _{OH3} =0.9·V _{DD} , V _{DD} =3.0V	SEG _{xx} (during DC output)	1.2		mA	1,3
	I _{OH3}			0.6		mA	1,3
Low-level output voltage	I _{OL1}	V _{OL1} =0.1·V _{DD} , V _{DD} =5.0V V _{OL1} =0.1·V _{DD} , V _{DD} =3.0V	P _{xx} , R _{xx}	8.5		mA	4
	I _{OL1}			4.1		mA	4
	I _{OL2}	V _{OL2} =0.1·V _{DD} , V _{DD} =5.0V V _{OL2} =0.1·V _{DD} , V _{DD} =3.0V	BZ	8.5		mA	4
	I _{OL2}			4.1		mA	4
	I _{OL3}	V _{OL3} =0.1·V _{DD} , V _{DD} =5.0V V _{OL3} =0.1·V _{DD} , V _{DD} =3.0V	SEG _{xx} (during DC output)	1.4		mA	1,4
	I _{OL3}			0.7		mA	1,4
Output leak current	I _{LOH}	V _{LOH} =V _{DD} V _{LOL} =V _{SS}	P _{xx} , R _{xx}	0		1.0	μA
	I _{LOL}			-1.0		0	μA
Common output current	I _{COMH}	V _{COMH} =V _{C3} -0.05V	COM _x			-5	μA
	I _{COML}	V _{COML} =V _{SS} +0.05V		5			μA
Segment output current	I _{SEGH}	V _{SEGH} =V _{C3} -0.05V	SEG _{xx} (during LCD output)			-5	μA
	I _{SEGJ}	V _{SEGJ} =V _{SS} +0.05V		5			μA

- Note) 1. When "DC output" is selected by mask option.
 2. When "LCD output" is selected by mask option.
 3. See "Characteristic Curves", for the maximum values.
 4. See "Characteristic Curves", for the minimum values.

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● Analog Circuit Characteristics

LCD Drive Voltage Characteristics

(Unless otherwise specified: VDD=2.7 to 5.5V, Vss=0V, Vc2/Vc1 are internal voltage, Ta=-20 to 85°C, C2=C3=0.1μF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
LCD supply voltage	Vc3l	Vc3	2.7		5.5	V	1
LCD drive voltage (when 1/3 bias is selected)	Vc1	Connect 1 MΩ load resistor between Vss or VDD and Vc1 (without panel load)	Typ. - 0.2	Vc3·1/3	Typ. + 0.2	V	2
	Vc2	Connect 1 MΩ load resistor between Vss or VDD and Vc2 (=Vc1) (without panel load)	Typ. - 0.2	Vc3·2/3	Typ. + 0.2	V	2
LCD drive voltage (when 1/2 bias is selected)	Vc1&2	Connect 1 MΩ load resistor between Vss or VDD and Vc1(=Vc2)(without panel load), Vc1 and Vc2 are shorted	Typ. - 0.2	Vc3·1/2	Typ. + 0.2	V	2
Built-in resistance	RLCD	Resistance between Vc3 and Vss	30	50	100	kΩ	2

Note) 1. When "Internal power (external Vc3 is used)" is selected by mask option.

2. Vc3 = VDD when "Internal power (external Vc3 is not used)" is selected by mask option.

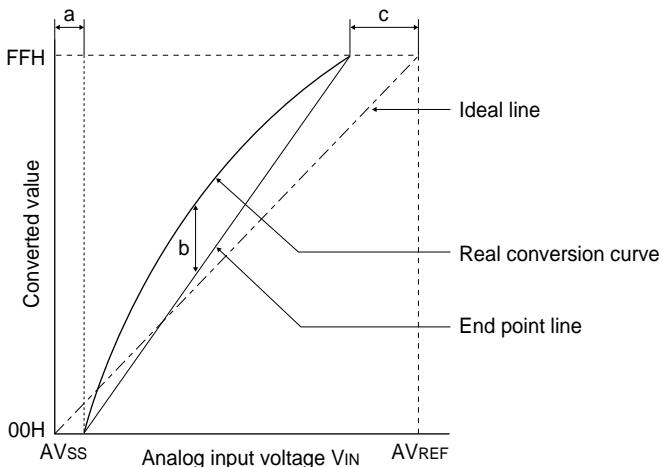
A/D Conversion Characteristics

(Unless otherwise specified: VDD=2.7 to 5.5V, Vss=AVss=0V, Ta=-20 to 85°C)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
Analog supply voltage	VAVDD	AVDD	2.7		VDD	V	
Analog reference voltage range	VREF	AVREF	2.7		AVDD	V	
Analog input voltage range	VIN	AD0 to AD3 (P40 to P43)	AVss		AVREF	V	
Analog input capacitance	CAIN	During sampling	AD0 to AD3 (P40 to P43)		35	pF	
Analog reference resistance	RREF	Resistance for AVREF–AVss		10	20	kΩ	
Resolution	—				8	bit	
Offset error	EOFF	AVDD=2.7V to VDD	-1		1	LSB	1
Full scale error	EFS	AVREF=2.7V to AVDD	-1		1	LSB	1
Non-linearity error	ELI	fAD=240kHz to 2.5MHz	-2		4	LSB	1,2
Overall error	ET		-2		4	LSB	1,2
A/D conversion time	tADC	fAD=240kHz to 2.5MHz	20		21	clock	1
Sampling time	tsMP	fAD=240kHz to 2.5MHz			8	clock	1

Note) 1. fAD=fPRS=fosc/2n or fAD=fOSC/2 (fAD: A/D conversion clock frequency, fosc: oscillation clock frequency, n=1–16: PRSM setting value + 1)

2. The best straight line within a ±3LSB of error can be obtained by correcting the conversion result with -1LSB by software.



Offset error : EOFF = a (the deviation from the ideal value at zero point)

Non-linearity error : ELI = b (the deviation of the real conversion curve from the end point line)

Full scale error : EFS = c (the deviation from the ideal value at the full scale point)

Total error : ET = max (EOFF, ELI, EABS)

EABS = the deviation from the ideal line (including quantizing error)

● Current Consumption

(Unless otherwise specified: V_{DD}=AV_{DD}=AV_{REF}=2.7 to 5.5V, V_{SS}=AV_{SS}=0V, Ta=25°C, C₁=0.1μF, C₂=C₃=0.1μF)

Characteristic	Symbol	Condition		Min.	Typ.	Max.	Unit	Note
Power current during SLEEP	I _{SLEEP}				0.3	1.0	μA	
Power current during HALT	I _{HALT}	LCD system circuit and A/D convertor are not used	Crystal oscillation (4.194304MHz)		560	1200	μA	1,4,7
			Ceramic oscillation (4.0MHz)		610	1400	μA	2,4,7
			CR oscillation (2MHz)		680	1400	μA	3,4,7
			External clock input (4.0MHz)		220	420	μA	4,7
Power current during execution	I _{EXEC}	LCD system circuit and A/D convertor are not used Software duty = 100%	Crystal oscillation (4.194304MHz)		1400	2600	μA	1,5,7
			Ceramic oscillation (4.0MHz)		1400	2600	μA	2,5,7
			CR oscillation (2MHz)		1100	2100	μA	3,5,7
			External clock input (4.0MHz)		1000	1700	μA	5,7
LCD system operating current	I _{LCD}	V _{DD} =V _{C3} =3.0V, no panel load			60	100	μA	8
		V _{DD} =V _{C3} =5.0V, no panel load			100	170	μA	8
A/D conversion operating current	I _{A/D}	V _{DD} =AV _{DD} =AV _{REF} =3.0V, f _{A/D} =262kHz			600	1000	μA	6
		V _{DD} =AV _{DD} =AV _{REF} =5.0V, f _{A/D} =262kHz			1800	3000	μA	6

Note) 1. R_f=1MΩ, C_G=C_D=15pF2. R_f=1MΩ, C_G=C_D=30pF3. R_{CR}=20kΩ

4. OSC: oscillated (except for external clock input) CPU, ROM, RAM: HALT status Others: stopped

5. OSC: oscillated (except for external clock input) CPU, ROM, RAM: operating Others: stopped

6. f_{A/D}=f_{PRRS}=f_{OSC}/2n (f_{A/D}: A/D conversion clock frequency, f_{OSC}: oscillation clock frequency, n=1~16: PRSM setting value + 1)
f_{OSC}=4.194304MHz, PRSM=7

7. Current consumption when the LCD system circuit or A/D converter is used is found by adding the LCD system operating current or the A/D conversion current.

8. When "Internal power" is selected by mask option.

● AC Characteristics

Operating Range

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, Ta=-20 to 85°C)

Characteristic	Symbol	Condition		Min.	Typ.	Max.	Unit	Note
Operating clock frequency	f _{OSC}	Crystal oscillation circuit		0.5		4.5	MHz	1
		Ceramic oscillation circuit		0.5		4.5	MHz	1
		CR oscillation circuit		0.5		2.5	MHz	1
		External clock input		0.5		4.5	MHz	1,2
Instruction execution time	t _{CY}	1-cycle instruction		0.44 (0.8)		4.0	μS	3
		2-cycle instruction		0.89 (1.6)		8.0	μS	3
		3-cycle instruction		1.33 (2.4)		12.0	μS	3

Note) 1. The CPU uses the clock output from the oscillation circuit as the operating clock.

2. When an external clock is input from the OSC3 terminal by setting the mask option, do not connect anything to the OSC4 terminal.

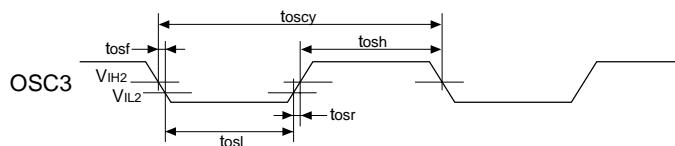
3. The values enclosed with () indicate the execution time when the CR oscillation circuit is used.

Input Clock

• OSC3 external clock

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, Ta=-20 to 85°C, V_{IH2}=1.7V, V_{IL2}=0.7V)

Characteristic	Symbol	Condition		Min.	Typ.	Max.	Unit	Note
Input clock cycle time	t _{OSCY}			230		2,000	nS	
Input clock "H" pulse width	t _{OSH}			115		1,000	nS	
Input clock "L" pulse width	t _{OL}			115		1,000	nS	
Input clock rising time	t _{OSR}					25	nS	
Input clock falling time	t _{OFS}					25	nS	



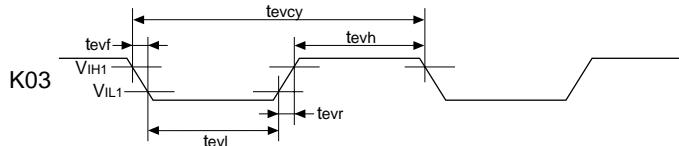
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• K03 external clock (event counter external clock)

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, Ta=-20 to 85°C, V_{IH1}=0.8·V_{DD}, V_{IL1}=0.2·V_{DD})

Characteristic	Symbol	Condition	Min.	Max.	Unit	Note
Input clock cycle time	tevcy	With noise rejecter	512·n/fosc		S	1
Input clock "H" pulse width	tevh		256·n/fosc		S	1
Input clock "L" pulse width	tevl		256·n/fosc		S	1
Input clock cycle time	tevcy	Without noise rejecter	4		μS	
Input clock "H" pulse width	tevh		2		μS	
Input clock "L" pulse width	tevl		2		μS	
Input clock rising time	tosr			25	nS	
Input clock falling time	tosf			25	nS	

Note) 1. fosc: oscillation clock frequency, n=1–16: PRSM setting value + 1



• RESET input clock

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, Ta=-20 to 85°C, V_{IH}=0.5·V_{DD}, V_{IL}=0.1·V_{DD})

Characteristic	Symbol	Condition	Min.	Max.	Unit	Note
RESET input time	t _{sr}		100		μS	



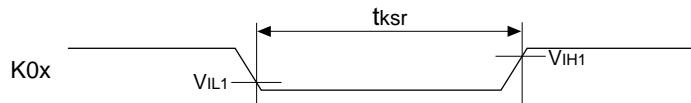
• K00–K03 simultaneous low input clock

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, Ta=-20 to 85°C, V_{IH1}=0.8·V_{DD}, V_{IL1}=0.2·V_{DD})

Characteristic	Symbol	Condition	Min.	Max.	Unit	Note
Simultaneous low input time	t _{ksr}	Time authorize circuit is used	524288·n/fosc		S	1
		Time authorize circuit is not used	768·n/fosc		S	1

Note) 1. fosc: oscillation clock frequency, n=1–16: PRSM setting value + 1

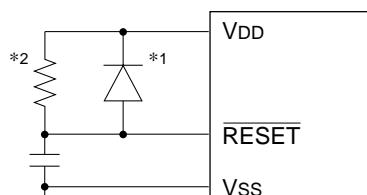
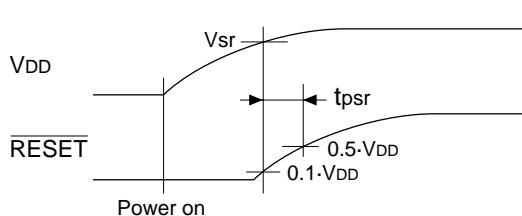
When the simultaneous low input reset function is selected by mask option.



Power-on Reset

(Unless otherwise specified: V_{SS}=0V, Ta=-20 to 85°C, V_{IH}=0.5·V_{DD}, V_{IL}=0.1·V_{DD})

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
Operating power voltage	V _{sr}	RESET=0.1·V _{DD}	2.7			V	
RESET input time	t _{psr}		100			μS	



*1 Because the potential of the RESET terminal not reached V_{DD} level or higher.

*2 When the built-in pull-up resistor is not used.

A/D Conversion Characteristics

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=AV_{SS}=0V, Ta=-20 to 85°C)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
A/D conversion time	t _{AADC}	f _{AADC} =240kHz to 2.5MHz	20		21	clock	1
Sampling time	t _{smp}	f _{AADC} =240kHz to 2.5MHz		8		clock	1

Note) 1. f_{AADC}=f_{PRS}=f_{osc}/2n or f_{AADC}=f_{osc}/2 (f_{AADC}: A/D conversion clock frequency, f_{osc}: oscillation clock frequency, n=1–16: PRSM setting value + 1)

● Oscillation Characteristics

Oscillation characteristics change depending on conditions (board pattern, components used, etc.). Use the following characteristics as reference values. In particular, when a ceramic oscillator or crystal oscillator is used, use the oscillator manufacturer's recommended values for constants such as capacitance and resistance.

Crystal Oscillation Circuit

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, T_A=-20 to 85°C, Crystal oscillator: CA301 4.194304MHz*, R_f=1MΩ, C_G=C_D=15pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
Oscillation start voltage	V _{STA}		2.7			V	
Oscillation start time	t _{STA}				20	mS	1
Oscillation stop voltage	V _{STP}		2.7			V	
Built-in gate capacitance	C _G			16		pF	
Built-in drain capacitance	C _D			13		pF	
Frequency/IC deviation	Δf/ΔIC		-10		10	ppm	
Frequency/supply voltage deviation	Δf/ΔV				1	ppm/V	
Permitted leak resistance	R _{LEAK}	Between OSC1 and V _{SS}	200			MΩ	

* CA301 4.194304MHz: made by Seiko Epson

Note) 1. The crystal oscillation start time varies according to the crystal oscillator, C_G and C_D to be used.

Ceramic Oscillation Circuit

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, T_A=-20 to 85°C, Ceramic oscillator: CSA 4.00MG*, R_f=1MΩ, C_G=C_D=30pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
Oscillation start voltage	V _{STA}		2.7			V	
Oscillation start time	t _{STA}				5	mS	
Oscillation stop voltage	V _{STP}		2.7			V	

* CSA 4.00MG: made by Murata Mfg. Co.

CR Oscillation Circuit

(Unless otherwise specified: V_{DD}=2.7 to 5.5V, V_{SS}=0V, T_A=-20 to 85°C)

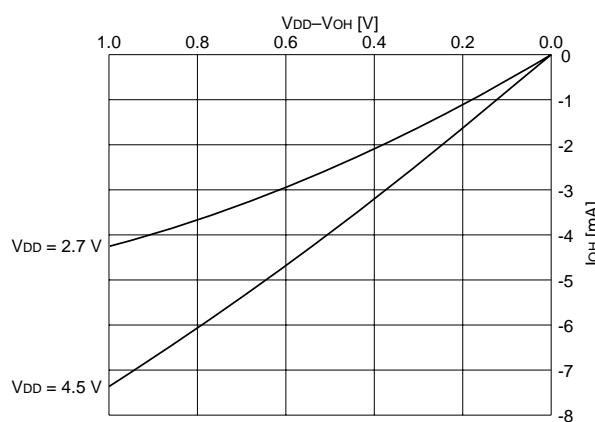
Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
Oscillation start voltage	V _{STA}		2.7			V	
Oscillation start time	t _{STA}				1	mS	
Oscillation stop voltage	V _{STP}		2.7			V	
Frequency/IC deviation	Δf/ΔIC	R _{CR} = constant	-25		25	%	

● Characteristic Curves (reference value)

Output Current Characteristics

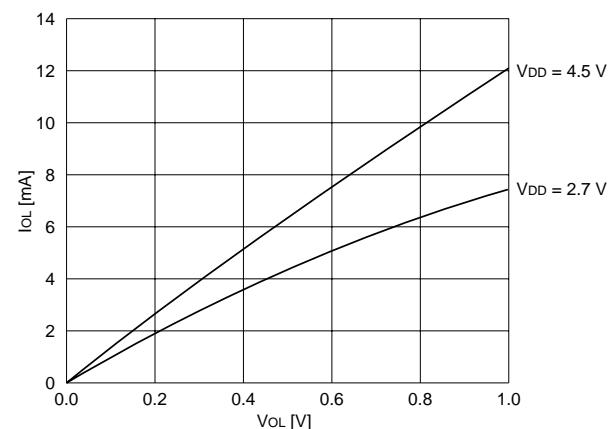
• High level output current (P_{xx}, R_{xx}, BZ)

T_A = 85°C, Max. value



• Low level output current (P_{xx}, R_{xx}, BZ)

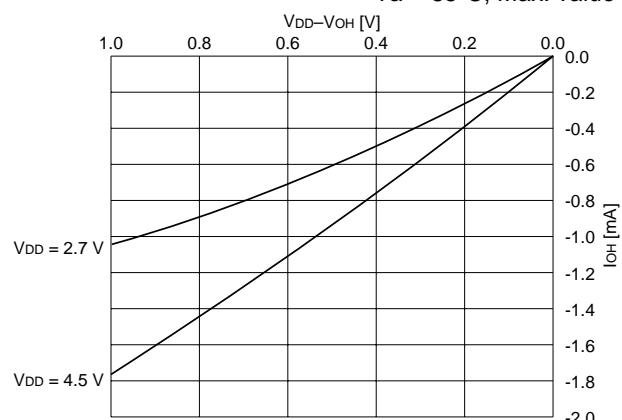
T_A = 85°C, Min. value



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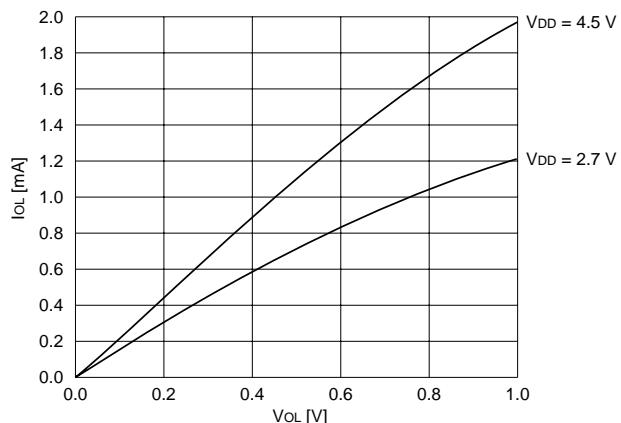
- High level output current (SEGxx)

T_a = 85°C, Max. value



- Low level output current (SEGxx)

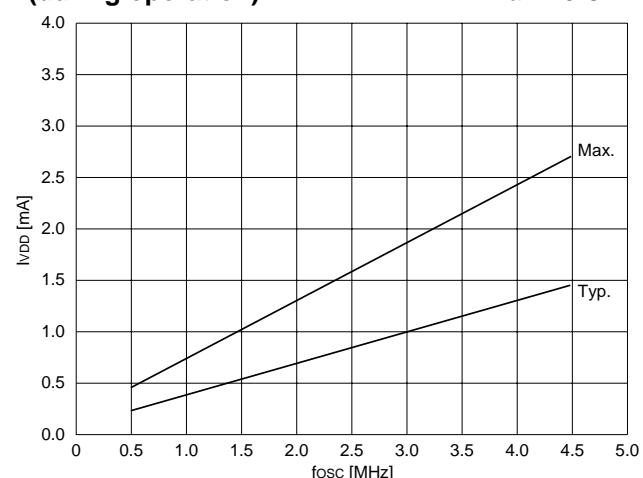
T_a = 85°C, Min. value



Power Current - Frequency Characteristics

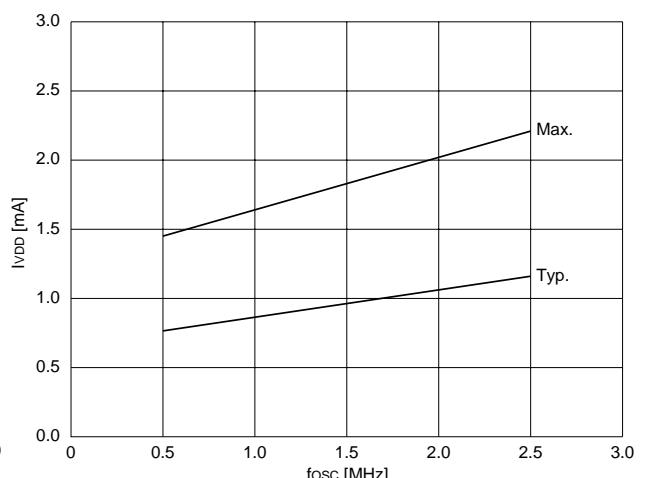
- Crystal oscillation/ceramic oscillation (during operation)

T_a = 25°C



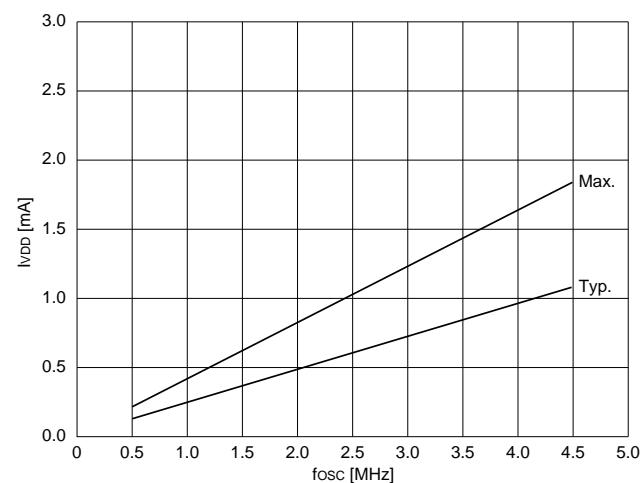
- CR oscillation (during operation)

T_a = 25°C



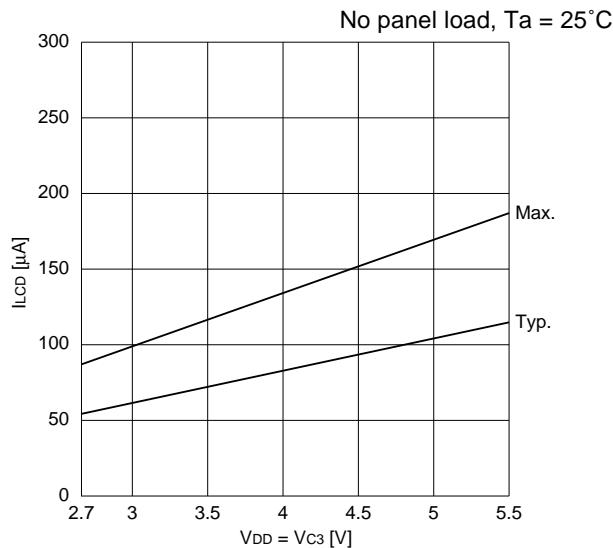
- External clock (during operation)

T_a = 25°C

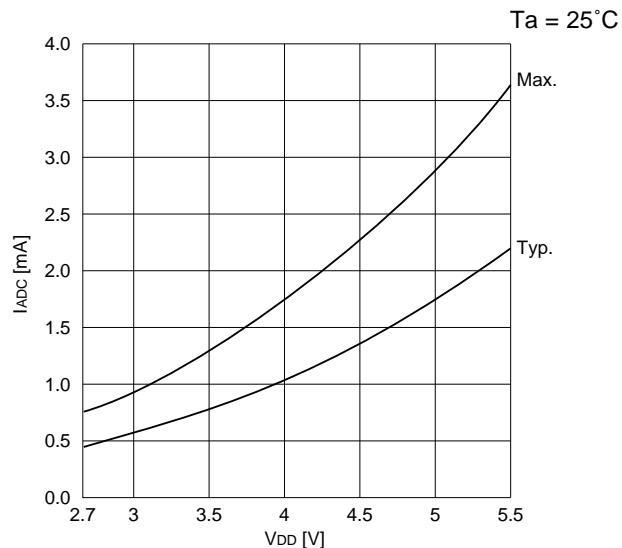


Analog System Operating Current - Voltage Characteristic

- LCD system operating current**



- A/D converter operating current**



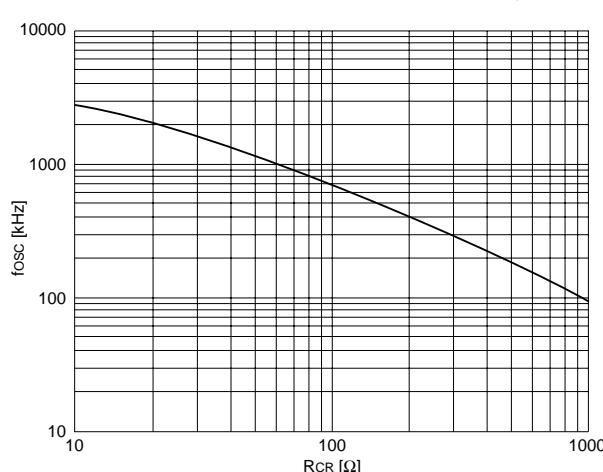
Note: Since the A/D converter operating current varies according to the A/D conversion clock frequency (f_{AD}) and analog input voltage, use the following voltage characteristics only for reference.

CR Oscillation Frequency Characteristics

Oscillation frequency changes depending on the conditions (components used, board pattern, etc.). In particular, extensively depending on the product from (chip, plastic package or ceramic package) and board capacitance. Therefore, use the following chart for reference only and select the resistance value after evaluating the actual product.

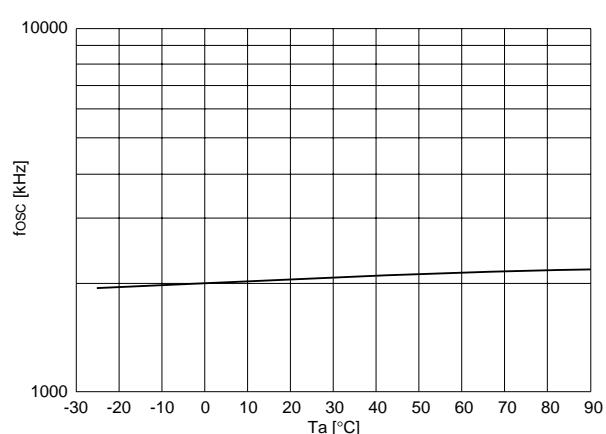
- Oscillation frequency - resistance characteristic**

$T_a = 25^\circ\text{C}$, Typ. value



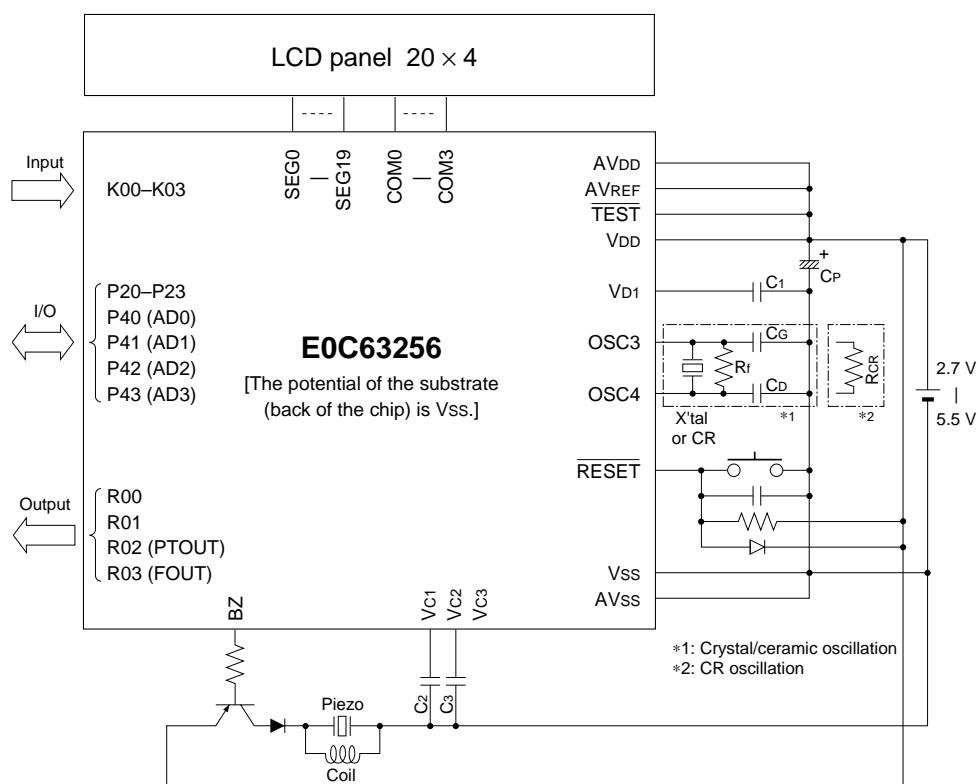
- Oscillation frequency - temperature characteristic**

$RCR = 20 \text{ k}\Omega$



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■ BASIC EXTERNAL CONNECTION DIAGRAM



X'tal	Crystal oscillator	4.194304 MHz
CR	Ceramic oscillator	4.0 MHz
Cg	Gate capacitor	15 pF (Crystal oscillation) 30 pF (Ceramic oscillation)
Cd	Drain capacitor	15 pF (Crystal oscillation) 30 pF (Ceramic oscillation)
Rf	Feedback resistor	1 MΩ
RCR	Resistor for CR oscillation	20 kΩ (2 MHz)
C1	Capacitor	0.1 μF
C2, C3	Capacitor	0.1 μF
CP		3.3 μF

Note: The above table is simply an example, and is not guaranteed to work.

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